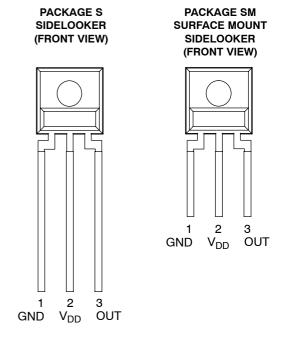


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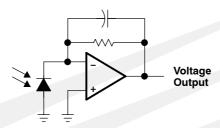
- Converts Light Intensity to Output Voltage
- Monolithic Silicon IC Containing Photodiode, Transconductance Amplifier, and Feedback Components
- Single-Supply Operation . . . 2.7 V to 5.5 V
- High Irradiance Responsivity . . . Typical 246 mV/(μW/cm²) at λ<sub>p</sub> = 640 nm (TSL12S)
- Low Supply Current . . . 1.1 mA Typical
- Sidelooker 3-Lead Plastic Package
- RoHS Compliant (-LF Package Only)



### **Description**

The TSL12S, TSL13S, and TSL14S are cost-optimized, highly integrated light-to-voltage optical sensors, each combining a photodiode and a transimpedance amplifier (feedback resistor =  $80~M\Omega$ ,  $20~M\Omega$ , and  $5~M\Omega$ , respectively) on a single monolithic integrated circuit. The photodiode active area is  $0.5~mm \times 0.5~mm$  and the sensors respond to light in the range of 320 nm to 1050 nm. Output voltage is linear with light intensity (irradiance) incident on the sensor over a wide dynamic range. These devices are supplied in a 3-lead clear plastic sidelooker package (S). When supplied in the lead (Pb) free package, the device is RoHS compliant.

### **Functional Block Diagram**



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### **Available Options**

DEVICE	T <sub>A</sub>	PACKAGE - LEADS	PACKAGE DESIGNATOR	ORDERING NUMBER
TSL12S	0°C to 70°C	3-lead Sidelooker	S	TSL12S
TSL12S	0°C to 70°C	3-lead Sidelooker — Lead (Pb) Free	S	TSL12S-LF
TSL12S	0°C to 70°C	3-lead Surface-Mount Sidelooker — Lead (Pb) Free	SM	TSL12SM-LF
TSL13S	0°C to 70°C	3-lead Sidelooker	S	TSL13S
TSL13S	0°C to 70°C	3-lead Sidelooker — Lead (Pb) Free	S	TSL13S-LF
TSL13S	0°C to 70°C	3-lead Surface-Mount Sidelooker — Lead (Pb) Free	SM	TSL13SM-LF
TSL14S	0°C to 70°C	3-lead Sidelooker	S	TSL14S
TSL14S	0°C to 70°C	3-lead Sidelooker — Lead (Pb) Free	S	TSL14S-LF
TSL14S	0°C to 70°C	3-lead Surface-Mount Sidelooker — Lead (Pb) Free	SM	TSL14SM-LF

### **Terminal Functions**

TERMINAL		TYPE	DESCRIPTION						
NAME	NAME NO.								
GND	1		Power supply ground (substrate). All voltages are referenced to GND.						
OUT	3	0	Output voltage.						
$V_{DD}$	2		Supply voltage.						

### Absolute Maximum Ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage, V <sub>DD</sub> (see Note 1)	
Output current, I <sub>O</sub>	±10 mA
Duration of short-circuit current at (or below) 25°C (see Note 2)	5 s
Operating free-air temperature range, T <sub>A</sub>	–25°C to 85°C
Storage temperature range, T <sub>stq</sub>	–25°C to 85°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds (S Package) .	
Reflow solder, in accordance with J-STD-020C or J-STD-020D (SM Package)	260°C

<sup>&</sup>lt;sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to GND.

2. Output may be shorted to supply.

### **Recommended Operating Conditions**

	MIN	NOM MAX	UNIT
Supply voltage, V <sub>DD</sub>	2.7	5.5	V
Operating free-air temperature, T <sub>A</sub>	0	70	°C



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# Electrical Characteristics at $V_{DD}$ = 5 V, $T_A$ = 25°C, $\lambda_p$ = 640 nm, $R_L$ = 10 k $\Omega$ (unless otherwise noted) (see Notes 3, 4, 5)

DADAMETED		TEGT CONDITIONS	TSL12S			1	SL13S		1			
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
$V_{OM}$	Maximum output voltage		4.6	4.9		4.6	4.9		4.6	4.9		V
		$E_e = 8 \mu W/cm^2$	1.5	2	2.5							
		$E_e = 31 \mu W/cm^2$				1.5	2	2.5				
l.,	Output voltage	$E_e = 120 \mu W/cm^2$							1.5	2	2.5	V
Vo		$E_e = 16 \mu\text{W/cm}^2$		4								
		$E_e = 62  \mu W/cm^2$					4					
		$E_e = 240 \ \mu W/cm^2$								4		
R <sub>e</sub>	Irradiance responsivity	Note 6		248			64		16			mV/ (μW/ cm <sup>2</sup> )
Vos	Extrapolated offset voltage	Note 6	-0.02	0.03	0.08	-0.02	0.03	0.08	-0.02	0.03	0.08	V
$V_{d}$	Dark voltage	E <sub>e</sub> = 0	0		0.08	0		0.08	0		0.08	V
	Supply current	$E_e = 8 \mu W/cm^2$		1.1	1.7							
I <sub>D</sub>		$E_e = 31 \mu W/cm^2$					1.1	1.7				mA
		$E_e = 120  \mu W/cm^2$								1.1	1.7	

NOTES: 3. Measurements are made with R  $_{L}$  = 10  $k\Omega$  between output and ground.

- 4. Optical measurements are made using small-angle incident radiation from an LED optical source.
- 5. The 640 nm input irradiance  $E_e$  is supplied by an AlInGaP LED with peak wavelength  $\lambda_p$  = 640 nm.
- 6. Irradiance responsivity is characterized over the range V<sub>O</sub> = 0.2 to 4 V. The best-fit straight line of Output Voltage V<sub>O</sub> versus irradiance E<sub>e</sub> over this range may have a positive or negative extrapolated V<sub>O</sub> value for E<sub>e</sub> = 0. For low irradiance values, the output voltage V<sub>O</sub> versus irradiance E<sub>e</sub> characteristic is non linear with a deviation toward V<sub>O</sub> = 0, E<sub>e</sub> = 0 origin from the best-fit straight line referenced above.

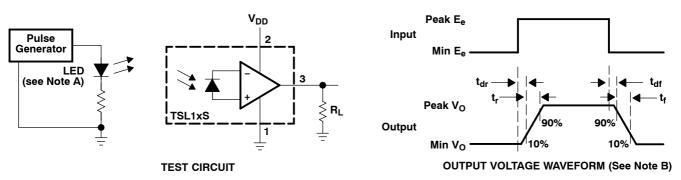
# Dynamic Characteristics at $V_{DD}$ = 5 V, $T_A$ = 25°C, $\lambda_p$ = 640 nm, $R_L$ = 10 k $\Omega$ (unless otherwise noted) (see Figure 1)

	DADAMETED	TEST CONDITIONS	TSL12S			1	rsL13S	1	TSL14S			UNIT	
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNII	
t <sub>dr</sub>	Output pulse delay	Min $V_O = 0 V$ ; Peak $V_O = 2 V$		13			1.7			0.9			
	time for rising edge (0% to 10%)	Min $V_O = 0.5 V$ ; Peak $V_O = 2 V$		2.3			1.2			0.6		μS	
	Output pulse rise time (10% to 90%)	Min $V_O = 0 V$ ; Peak $V_O = 2 V$		20			7.2			2.6			
t <sub>r</sub>		Min $V_O = 0.5 V$ ; Peak $V_O = 2 V$		10			6.5			2.9		μS	
	Output pulse delay time for falling edge (100% to 90%)	Min $V_O = 0 V$ ; Peak $V_O = 2 V$		2.3			1.2			8.0			
t <sub>df</sub>		$Min V_O = 0.5 V; Peak V_O = 2 V$		2.2			1.1			0.7		μS	
	Output pulse fall time	ut pulse fall time Min $V_0 = 0 \text{ V}$ ; Peak $V_0 = 2 \text{ V}$ 10			6.8			2.9					
t <sub>f</sub>	(90% to 10%)	$Min V_O = 0.5 V; Peak V_O = 2 V$		9			6.4			2.8		μS	



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### PARAMETER MEASUREMENT INFORMATION

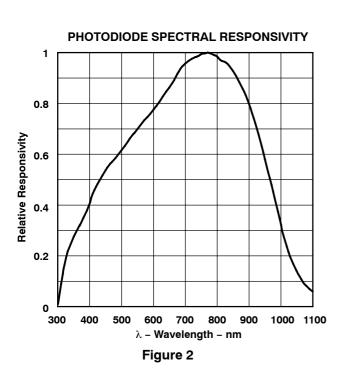


NOTES: A. The input irradiance is supplied by a pulsed AlInGaP light-emitting diode with the following characteristics:  $\lambda_p = 640$  nm,  $t_r < 1 \ \mu s$ .

B. The output waveform is monitored on an oscilloscope with the following characteristics:  $t_r < 100$  ns,  $Z_i \ge 1$  M $\Omega$ ,  $C_i \le 20$  pF.

Figure 1. Switching Times

### **TYPICAL CHARACTERISTICS**



### **NORMALIZED OUTPUT VOLTAGE** vs ANGULAR DISPLACEMENT 0.8 Normalized Output Voltage 0.6 Axis 0.4 Optical 0.2 80° 60° 40° **0**° 20° 40° 80° $\theta$ – Angular Displacement

Figure 3

### **TYPICAL CHARACTERISTICS**

### **TSL12S**

# RISING EDGE DYNAMIC CHARACTERISTICS vs.

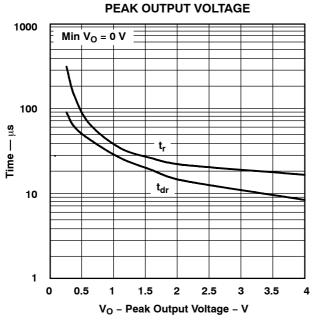


Figure 4

# RISING EDGE DYNAMIC CHARACTERISTICS vs.

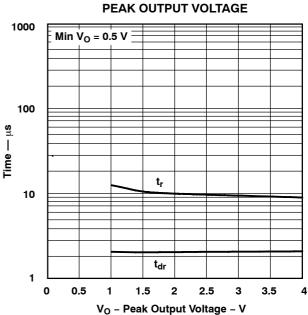
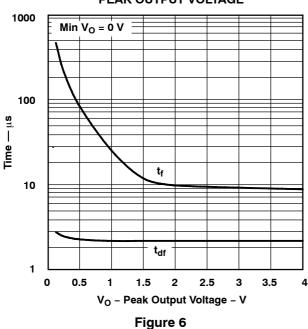


Figure 5

### FALLING EDGE DYNAMIC CHARACTERISTICS

## vs. PEAK OUTPUT VOLTAGE



### FALLING EDGE DYNAMIC CHARACTERISTICS

### vs. PEAK OUTPUT VOLTAGE

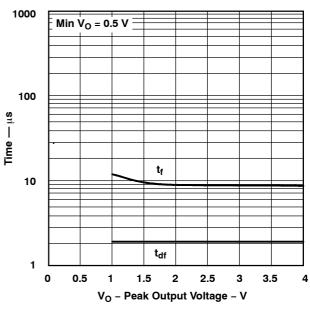


Figure 7

### **TYPICAL CHARACTERISTICS**

### **TSL13S**

# RISING EDGE DYNAMIC CHARACTERISTICS vs.

# PEAK OUTPUT VOLTAGE 20 Min V<sub>O</sub> = 0 V 16 t<sub>r</sub> 4 t<sub>dr</sub> 0 0 0.5 1 1.5 2 2.5 3 3.5 4 V<sub>O</sub> - Peak Output Voltage - V

Figure 8

# RISING EDGE DYNAMIC CHARACTERISTICS vs. PEAK OUTPUT VOLTAGE

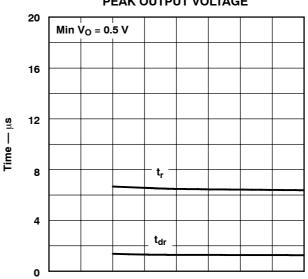
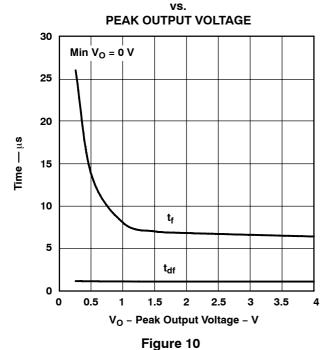


Figure 9

0.5

### FALLING EDGE DYNAMIC CHARACTERISTICS



FALLING EDGE DYNAMIC CHARACTERISTICS vs.

V<sub>O</sub> - Peak Output Voltage - V

3.5

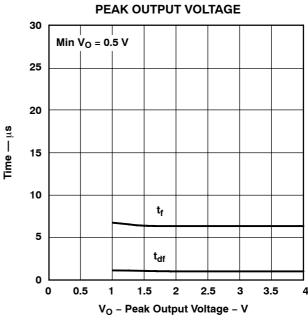


Figure 11

### **TYPICAL CHARACTERISTICS**

### TSL14S

# RISING EDGE DYNAMIC CHARACTERISTICS vs.

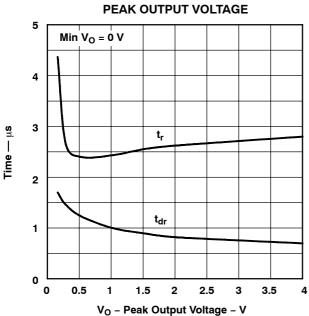


Figure 12

### vs. PEAK OUTPUT VOLTAGE

RISING EDGE DYNAMIC CHARACTERISTICS

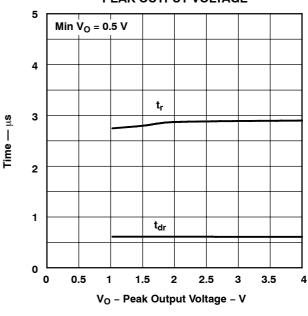


Figure 13

### FALLING EDGE DYNAMIC CHARACTERISTICS

# vs. PEAK OUTPUT VOLTAGE

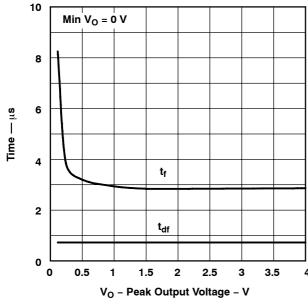


Figure 14

# FALLING EDGE DYNAMIC CHARACTERISTICS vs.

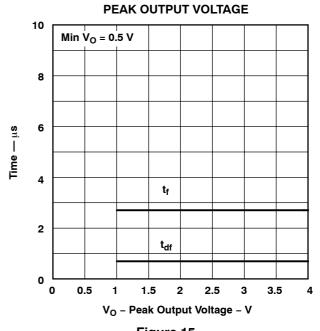


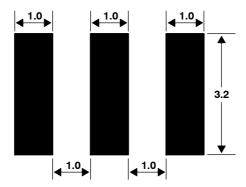
Figure 15

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### **APPLICATION INFORMATION**

### **PCB Pad Layout**

Suggested PCB pad layout guidelines for the SM surface mount package are shown in Figure 16.



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

Figure 16. Suggested SM Package PCB Layout

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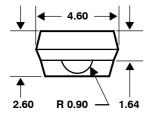
### **MECHANICAL DATA**

The TSL12S, TSL13S, and TSL14S are supplied in a clear 3-lead through-hole package with a molded lens.

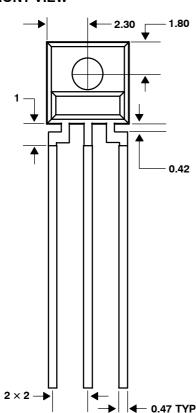
### **PACKAGE S**

### PLASTIC SINGLE-IN-LINE SIDE-LOOKER PACKAGE

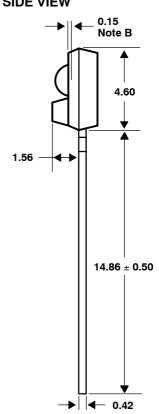
### **TOP VIEW**



### **FRONT VIEW**



### **SIDE VIEW**



NOTES: A. All linear dimensions are in millimeters; tolerance is ± 0.25 mm unless otherwise stated.

- B. Dimension is to center of lens arc, which is located below the package face.
- C. The 0.50 mm × 0.50 mm integrated photodiode active area is typically located in the center of the lens and 0.97 mm below the top of the lens surface.

**Available** 

- D. Index of refraction of clear plastic is 1.55.
- E. Lead finish for TSL1xS: solder dipped, 63% Sn/37% Pb. Lead finish for TSL1xS-LF: solder dipped, 100% Sn.
- F. This drawing is subject to change without notice.

Figure 17. Package S — Single-In-Line Side-Looker Package Configuration

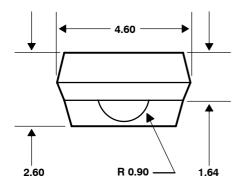


### **MECHANICAL DATA**

### **PACKAGE SM**

### PLASTIC SURFACE MOUNT SIDE-LOOKER PACKAGE

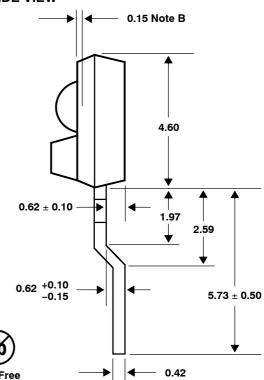
### **TOP VIEW**



### **FRONT VIEW**

# 2.30 1.80 1.80 2 × 2 → 0.47 TYP

### **SIDE VIEW**



NOTES: A. All linear dimensions are in millimeters; tolerance is  $\pm$  0.25 mm unless otherwise stated.

- B. Dimension is to center of lens arc, which is located below the package face.
- C. The integrated photodiode active area is typically located in the center of the lens and 0.97 mm below the top of the lens surface.
- D. Index of refraction of clear plastic is 1.55.
- E. Lead finish for TSL1xSM-LF: solder dipped, 100% Sn.
- F. This drawing is subject to change without notice.

Figure 18. Package SM — Surface Mount Side-Looker Package Configuration



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